

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device has a semiconductor substrate ~~1~~; a first interlayer insulating film ~~2~~ ~~formed~~ on the semiconductor substrate, and having first contact holes; first contact plugs ~~12 and 13~~ ~~formed on the first interlayer insulating film 2~~ and having portions buried in the first contact holes and portions ~~protruded~~ protruding from the surface of the first interlayer insulating film ~~2~~; sidewalls ~~15~~ ~~formed~~ on the sides of the ~~protruded~~ protruding portions of the first contact plugs ~~12 and 13~~; a second interlayer insulating film ~~16~~ ~~formed~~ on the first interlayer insulating film ~~2~~, the first contact plugs ~~12 and 13~~, and the sidewalls ~~15~~, and having second contact holes; and second contact plugs ~~19 and 20~~ ~~formed on~~ in the second contact holes, and connected to the first contact plugs ~~12 and 13~~.